

05.13-04

Express Mail No. EV 346 810 952 US

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of: Bruce FAURE

Confirmation No. 7062

Application No.: 10/716,901

Group Art Unit: 2812

Filing Date: November 18, 2003

Examiner:

TED 1

Atty. Docket No.: 4717-12500

For: METHOD FOR FABRICATING A CARRIER

**SUBSTRATE** 

## SUPPLEMENTAL-INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents P.O. Box 1450 Alexandria, Virginia 22313-1450

Sir:

Pursuant to applicant's duty of disclosure under 37 C.F.R. 1.56, applicant submits herewith twenty-five (25) references for the Examiner's review and consideration. These references were cited in the European Search Report and a copy is enclosed.

These references are listed on the enclosed Form PTO-1449. It is respectfully requested that these references be made of record in this application by the Examiner's completion and return of the PTO Form 1449.

No fee is believed to be due for the filing of this statement as it is being submitted prior to an initial office action for this application. Should any fees be required, however, please charge such fees to Winston & Strawn LLP Deposit Account No. 50-1814.

Date: 5/11/04

Respectfully submitted,

Allan A. Fanucci

(Reg. No. 30,256)

WINSTON & STRAWN LLP CUSTOMER NO. 28765

(212) 294-3311

Enclosures

NY:863414.1



## LIST OF REFERENCES CITED BY APPLICANT (Use several sheets if necessary)

ATTY. DOCKET NO.:	APPLICATION NO.;		
4717-12500	10/716,901		
APPLICANT:			
Bruce FAURE			
FILING DATE:	GROUP:		
November 18, 2003	2812		

		<u> </u>				NT DOCUMENTS	100		ETI P.V	DATE II
EXAMINER INITIAL		DOCUMENT NUMBER	1	DATE		NAME	CLASS	SUBCLASS	APPRO	PRIATE
	AA	5,374,564	4/2000 7/2000 9/2000		Brue	1	437	24		
	AB	6,051,849			Davi	s et al.	257	103		
	AC	6,086,673			Molr	arq	117	102		
	AD	6,113,685			Wan	g et al.	117	3		
	AE	6,146,457			Solo	mon	117	90		
	AF 6,303,405 B1 10/2001 AG 6,440,823 B1 8/2002 AH 6,478,871 B1 11/2002		/2001			438	46			
			2002			438	478		·	
			/2002	Shea	ly et al.	117	84			
	ΑI	2002/0068201 A1			Vaud	lo et al.	428	704		
	AJ	2002/0011599 A1			Moto	Motoki et al.		76		
	<b>.</b>		•	FORE	IGN PA	TENT DOCUMENTS				
						CLASS	SUBCLASS	TRANS	LATION	
		DOCUMENT NUMBER		DAT	ГЕ	COUNTRY			YES	NO
	AK	EP 1 361 298 A1		11/200	03	Europe			X	
-	AL EP 1 298 234 A2 4/2002 AM FR 2 810 159 A1 12/200 AN FR 2 774 511 8/1999		4/2002	2	Europe			X		
			12/200	01	France			X		
			9	France			X			
	AO	FR 2 681 472	2 681 472 3/199		3	France			Х	
	AP JP 2002343718 with English Abstract 11/200  AQ WO 02064865 A1 with English Abstract 8/2002  AR WO 03/043066 A2 5/2003		11/200	02	Japan			x		
			2	PCT			X			
			3	PCT			x			

		ut uthor, Title, Date, Pertinent Pages, Etc.)				
AS	R. Lantier et al., "Influence of the first preparation steps on the properties of GaN layers grown on 6H-SIC by MBE", , MRS Internet J. Nitride Semicond. Res. 4S1, G3.50 (1999)					
AT	J. Cao et al, "Improved quality GaN by growth on compliant silicon-on-insulator substrates using metalorganic chemical vapor deposition", Journal of Applied Physics, Vol. 83, No.7, (1998).					
AU	AU Jyh-Rong Gong et al., "Influence of AIN/GaN strained multi-layers on threading dislocations in GaN films grown by alternate supply of metalorganics and NH <sub>3</sub> ", Materials Science and Engineering B94 pp. 155-1 58 (2002),					
AV	Motoaki Iwaya et al., "Realization of crack-free and high-quality thick AI <sub>x</sub> Ga <sub>1-x</sub> N for UV optoelectronics using low-temperature interlayer", Applied Surface Science Vol.159-160 pp. 405-413 (2000)					
AW	H. Amano et al., "Metalorganic vapor phase epitaxial growth of a high quality GaN film using an AIN buffer layer", Applied Physics Letters, Vol. 48, No. 5, pp. 353-355 (1986)					
AX	AX Y. Ujiie et al., "Epitaxial lateral overgrowth of GaAs on a Si substrate", Japanese Journal of Applied-Physics, Vol. 28, No. 3; pp. L337-L339 (1989)					
AY	AY B. Beaumont, Ph. et al., "Epitaxial lateral overgrowth of GaN", phys. stat. sol. (b) 227, No. 1, 1-43 (2001)					
AZ						
	EXAMINER	DATE CONSIDERED .				
*EXAMINER:		is in conformance with MPEP 609; Draw line through citation if not y of this form with next communication to applicant.				



To: Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

The following items listed below are being filed herewith with the USPTO on May 11, 2004

Express Mail No. <b>EV 346 810 952 US</b>					
Attorney Docket No.	Appln. Serial No./ Patent No.	Items - Documents filed on May 10, 2004			
4717-12500	10/716,901	Supplemental Information Disclosure Statement, PTO 1449, 25 refs.			

Please acknowledge receipt of these items as received by returning the enclosed postcards with the date of receipt of May 11, 2004

NY:863041.2